

CLAIMS

What is claimed is:

- 1 1. A method, comprising simulating a photolithographic mask for fabrication of an integrated
2 circuit, then simulating an image to be produced by that mask on a wafer.
- 1 2. The method of claim 1, further comprising correcting and/or optimizing the mask and/or
2 the simulation or image thereof.
- 1 3. The method of claim 2 wherein said correcting and/or optimizing comprises increasing or
2 decreasing at least one magnitude or value of (a) an optical proximity correction factor and/or
3 (b) a serif.
- 1 4. A method, comprising simulating optical proximity effects of a mask for fabrication of an
2 integrated circuit, and correcting corner rounding effects in an image produced by said mask.
- 1 5. The method of claim 3 wherein the optical proximity effects comprise effects of light
2 having a wavelength of approximately four times a feature size of said image.
- 1 6. A method, comprising incorporating corrections for corner rounding effects in an image
2 produced by an integrated circuit mask into an optical proximity correcting procedure by
3 adjusting an as-drawn layout of the mask as part of a computer aided design process.
- 1 7. The method of claim 6 wherein distortions are applied to corners and serifs in the mask.
- 1 8. A format for data input into or output from either or both simulating steps of claim 1, each
2 format being compatible with the other.